

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A gap fill material forming composition characterized in that the composition is used in manufacture of semiconductor device by a method comprising coating a photoresist on a substrate having a hole with aspect ratio shown in height/diameter of 1 or more, and transferring an image to the substrate by use of lithography process, and that the composition is coated on the substrate prior to coating of the photoresist, and comprises a polymer having a hydroxy group or a carboxy group and a crosslinking agent.
2. (Original) The gap fill material forming composition according to claim 1, wherein the polymer has a weight average molecular weight of 500 to 30000.
3. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing repeating unit having a hydroxy group or a carboxy group in main chain.
4. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing repeating unit having a hydroxy group or a carboxy group in side chain.
5. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing acrylic acid or methacrylic acid as repeating unit.

6. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing hydroxyalkyl acrylate or hydroxyalkyl methacrylate as repeating unit.

7. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a dextrin ester compound.

8. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing hydroxystyrene as repeating unit.

9. (Currently Amended) The gap fill material forming composition according to claim 1 ~~any one of claims 1 to 7~~, wherein the polymer has no aromatic ring structure in the structure.

10. (Original) The gap fill material forming composition according to claim 1, wherein the crosslinking agent is a crosslinking agent having at least two crosslink-forming functional groups.

11. (Currently Amended) The gap fill material forming composition according to claim 1 ~~any one of claims 1 to 10~~, further containing an alkali-dissolution rate regulator.

12. (Currently Amended) A method for forming a gap fill material layer for use in manufacture of semiconductor device comprising coating the gap fill material forming composition according to claim 1 ~~any one of claims 1 to 11~~ on a substrate and baking it.

13. (Currently Amended) A gap fill material layer manufactured by coating the gap fill

material forming composition according to claim 1~~any one of claims 1 to 11~~ on a semiconductor substrate and baking it, in which the gap fill material layer has a dissolution rate for an alkaline aqueous solution having a concentration of 0.1% to 20% ranging from 3 to 200 nm per second.